Dynamic Characteristics T_J = 25°C unless otherwise specified APT102GA60B2_L

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	Capacitance		8170		pF
C_{oes}	Output Capacitance	V_{GE} = 0V, V_{CE} = 25V		630		
C_{res}	Reverse Transfer Capacitance	f = 1MHz		78		
Q_g [4]	Total Gate Charge	Gate Charge		294		nC
Q_{ge}	Gate-Emitter Charge	V_{GE} = 15V		56		
Q_{gc}	Gate- Collector Charge	V_{CE}= 300V I_C = 62A		106		
SSOA	Switching Safe Operating Area	T_J = 150°C, R_G = 4.7Ω[5], V_{GE} = 15V, L= 100uH, V_{CE} = 600V	307			A
$t_{d(on)}$	Turn-On Delay Time	Inductive Switching (25°C) IGBT and Diode		28		ns
t_r	Current Rise Time	V_{CC} = 400V		37		
$t_{d(off)}$	Turn-Off Delay Time	V_{GE} = 15V		212		
t_f	Current Fall Time	I_C = 62A		101		
E_{on2}	Turn-On Switching Energy	R_G = 4.7Ω[5]		1354		µJ
E_{off} [7]	Turn-Off Switching Energy	T_J = +25°C		1614		
$t_{d(on}$	Turn-On Delay Time	Inductive Switching (125°C) IGBT and Diode		27		ns
t_r	Current Rise Time	V_{CC} = 400V		37		
$t_{d(off)}$	Turn-Off Delay Time	V_{GE} = 15V		247		
t_f	Current Fall Time	I_C = 62A		142		
E_{on2}	Turn-On Switching Energy	R_G = 4.7Ω[5]		2106		µJ
E_{off} [7]	Turn-Off Switching Energy	T_J = +125°C		1852		

1 Continuous current limited by package lead temperature.

2 Repetitive Rating: Pulse width and case temperature limited by maximum junction temperature.

3 Pulse test: Pulse Width < 380μs, duty cycle < 2%.

4 See Mil-Std-750 Method 3471.

5 R_G is external gate resistance, not including internal gate resistance or gate driver impedance. (MIC4452)

6 E_{on2} is the clamped inductive turn on energy that includes a commutating diode reverse recovery current in the IGBT turn on energy loss. A combi device is used for the clamping diode.

7 E_{off} is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1.

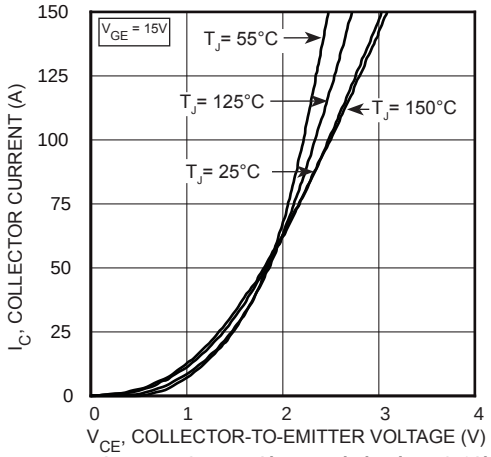


FIGURE 1, Output Characteristics (T_J = 25°C)

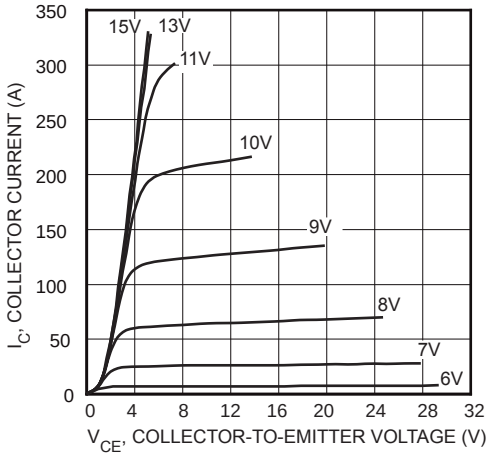


FIGURE 2, Output Characteristics (T_J = 25°C)

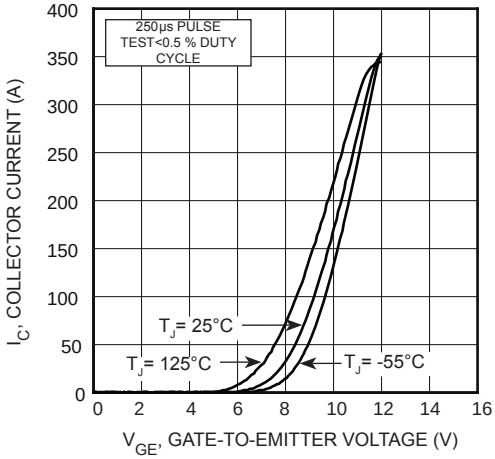


FIGURE 3, Transfer Characteristics

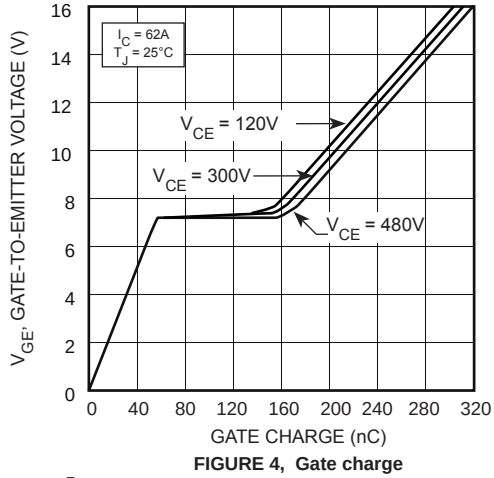


FIGURE 4, Gate charge

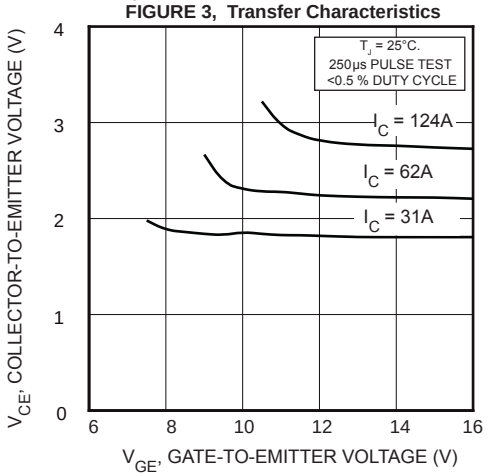


FIGURE 5, On State Voltage vs Gate-to-Emitter Voltage

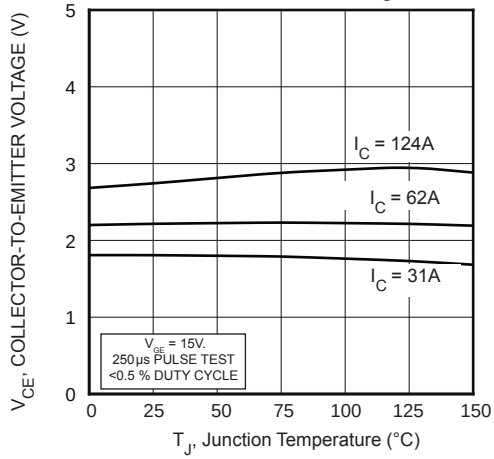


FIGURE 6, On State Voltage vs Junction Temperature

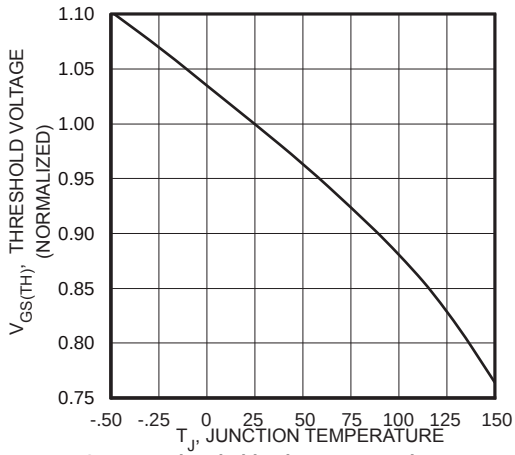


FIGURE 7, Threshold Voltage vs Junction Temperature

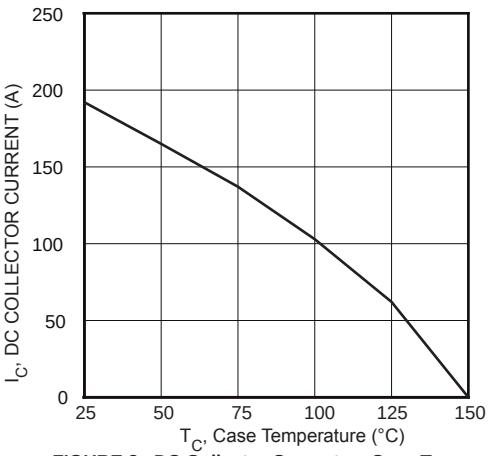


FIGURE 8, DC Collector Current vs Case Temperature

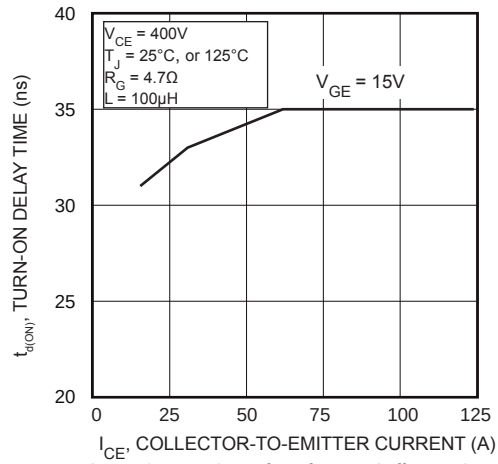


FIGURE 9, Turn-On Delay Time vs Collector Current

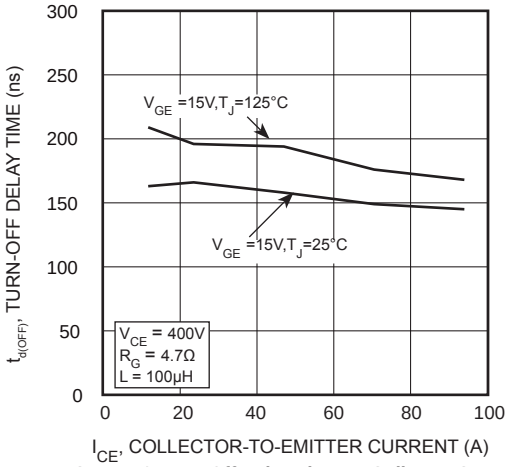


FIGURE 10, Turn-Off Delay Time vs Collector Current

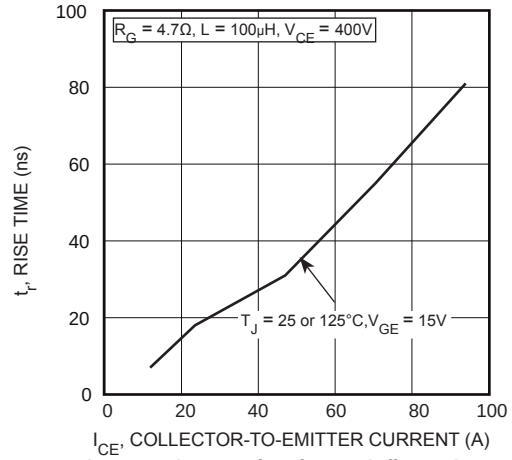


FIGURE 11, Current Rise Time vs Collector Current

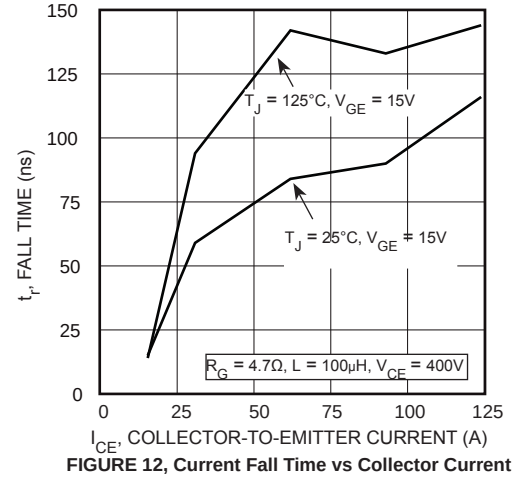


FIGURE 12, Current Fall Time vs Collector Current

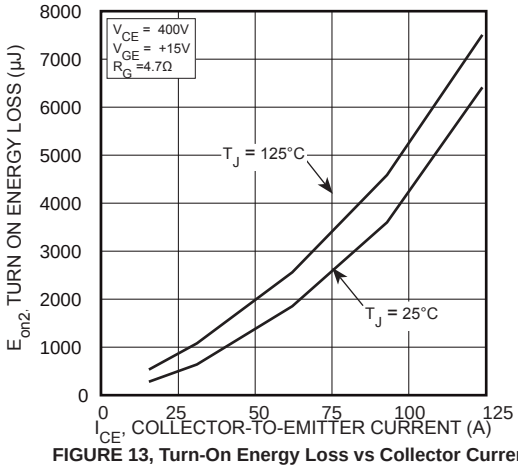


FIGURE 13, Turn-On Energy Loss vs Collector Current

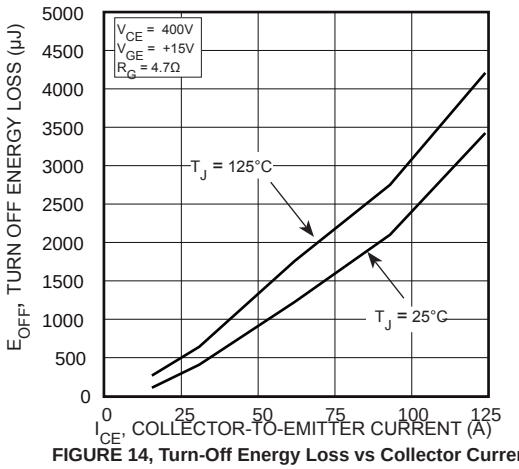


FIGURE 14, Turn-Off Energy Loss vs Collector Current

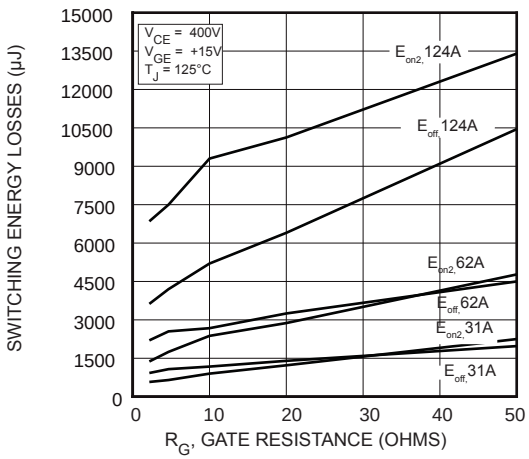


FIGURE 15, Switching Energy Losses vs Gate Resistance

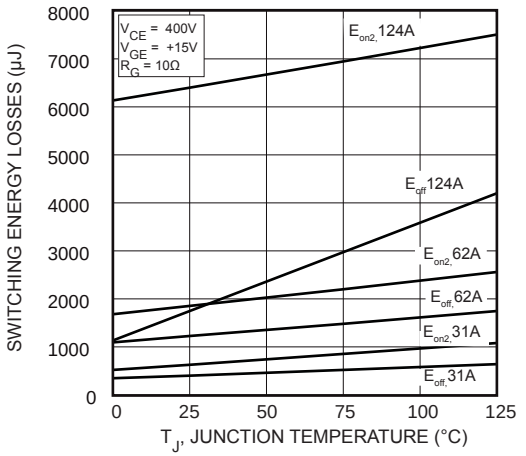


FIGURE 16, Switching Energy Losses vs Junction Temperature

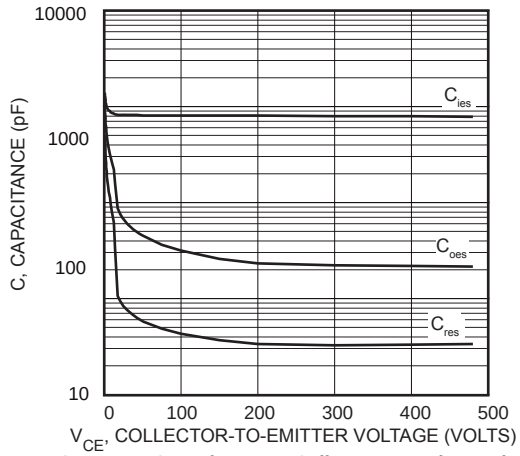


FIGURE 17, Capacitance vs Collector-To-Emitter Voltage

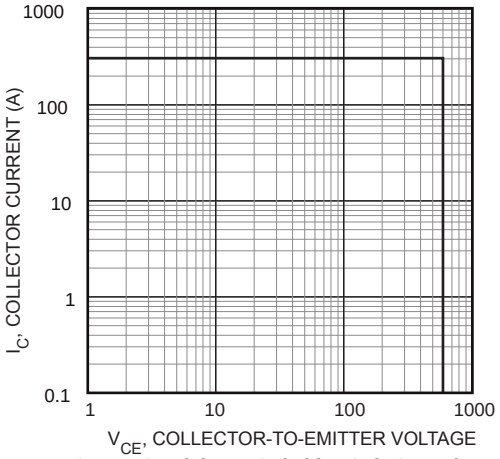


FIGURE 18, Minimum Switching Safe Operating Area

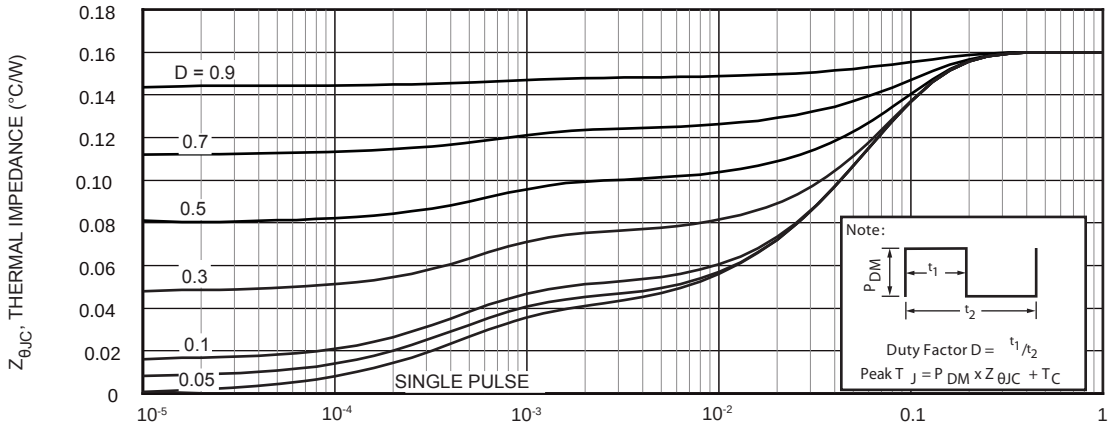


Figure 19, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

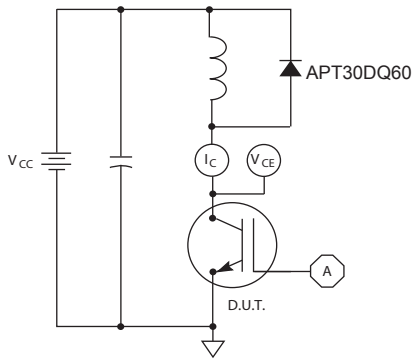


Figure 20, Inductive Switching Test Circuit

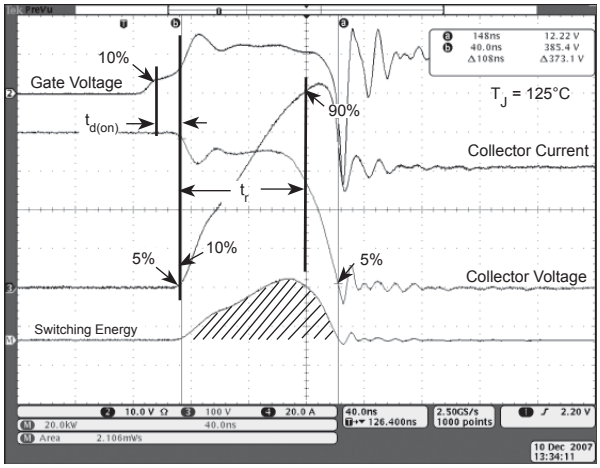


Figure 21, Turn-on Switching Waveforms and Definitions

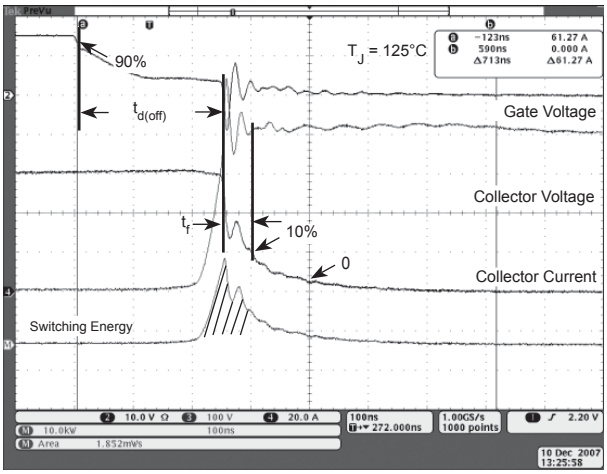
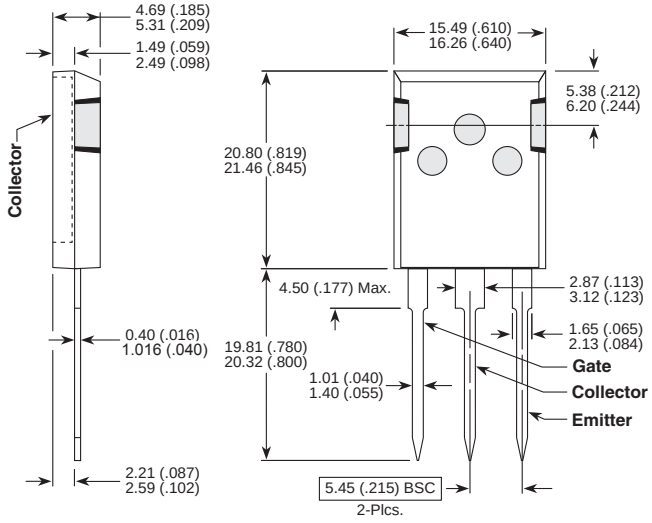


Figure 22, Turn-off Switching Waveforms and Definitions

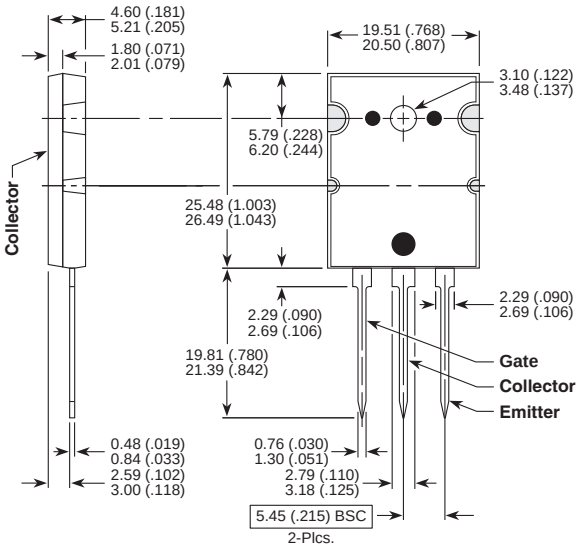
T-MAX™ (B2) Package Outline



These dimensions are equal to the TO-247 without the mounting hole.

Dimensions in Millimeters and (Inches)

TO-264 (L) Package Outline



Dimensions in Millimeters and (Inches)